

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2024/0213241 A1 JOU et al.

Jun. 27, 2024 (43) **Pub. Date:**

(54) ELECTROSTATIC DISCHARGE PROTECTION DEVICE

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(21) Appl. No.: 18/146,762

(22) Filed: Dec. 27, 2022

Publication Classification

(51) Int. Cl. H01L 27/02

(2006.01)

U.S. Cl. (52)

CPC H01L 27/0292 (2013.01); H01L 27/0262

(2013.01)

(57)ABSTRACT

An ESD protection device includes a substrate, an epitaxial layer, first to third well regions, and first to sixth doped regions. The first to third well regions are disposed in the epitaxial layer. The third well region is disposed between the first and second well regions. The first and second doped regions are disposed on the first well region and coupled to a pad. The third and fourth doped regions are disposed on the second well region and coupled to a ground terminal. The fifth doped region is disposed on the third well region, and the sixth doped region is disposed in the fifth doped region. The third, fifth, and sixth doped regions have the same conductive type. In response to an electrostatic discharge event occurring on the pad, a discharge path is formed between the pad and the ground terminal.

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